Polycrystalline Materials

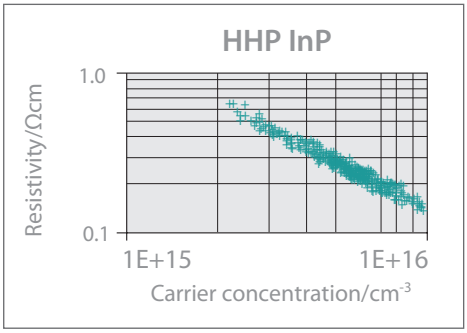
For use as source material and bulk crystal growth charges

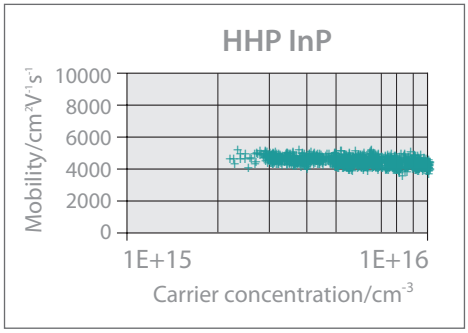
Polycrystalline ingots are produced by reacting at least 99.9999% (6N) pure elements together. The resulting stoichiometric compounds are then shaped, cleaned and individually packaged.

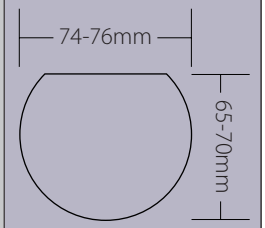
Both ends of each ingot are routinely assessed by Hall/Van der Pauw measurements to provide full electrical characterisation. Each synthesised batch is supplied with a complete Certificate of Conformance. Glow Discharge Mass Spectrographic (GDMS) purity analyses are performed on a sampling basis.

INDIUM PHOSPHIDE

Undoped, high purity InP is multiply refined and synthesised in a horizontal high pressure (HHP) furnace resulting in a polycrystalline ingot which can be supplied in ingot/ingot sections, slices or crushed granules.

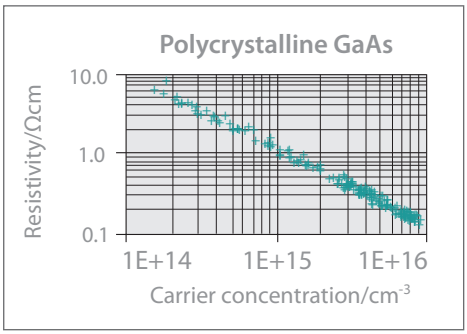


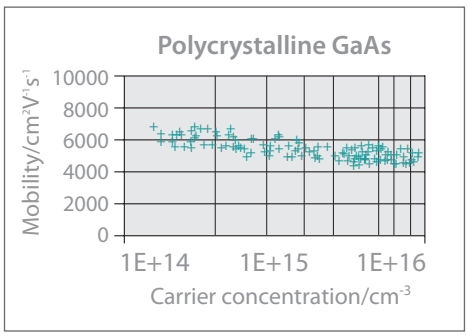


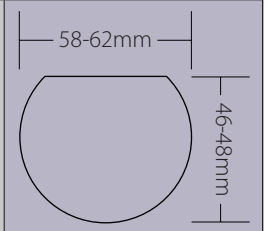
InP Ingot Specifications	
Dimensions	
Ingot Weight	Up to 7.5 kg
Gain Area (typical)	~ 5-10mm²
Maximum Carrier Concentration	Grade 1: 6 x 10^{15} cm^{-3} Grade 2: 1 x 10^{16} cm^{-3} Grade 3: 3 x 10^{16} cm^{-3}

GALLIUM ARSENIDE

Undoped, high purity GaAs is synthesised in a horizontal ingot form which can be supplied in ingot/ingot sections, slices or crushed granules.





GaAs Ingot Specifications	
Dimensions	
Ingot Weight	5 kg
Gain Area (typical)	~ 1-5cm²
Main Impurity	Si
Maximum Carrier Concentration	Grade 1: 1 x 10^{16} cm^{-3} Grade 2: 3 x 10^{16} cm^{-3}

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